

Fig. 1

Fig. 2A FORMATION OF GATE ELECTRODE AND GATE INSULATING FILM

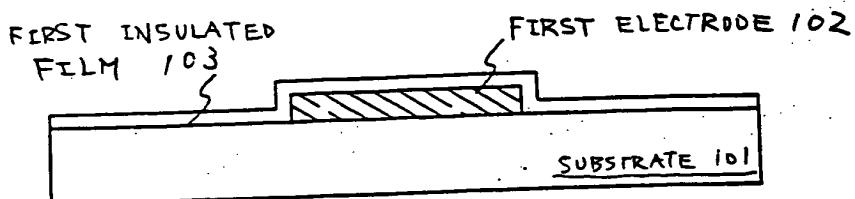


Fig. 2B FORMATION OF SECOND INSULATED FILM PATTERN

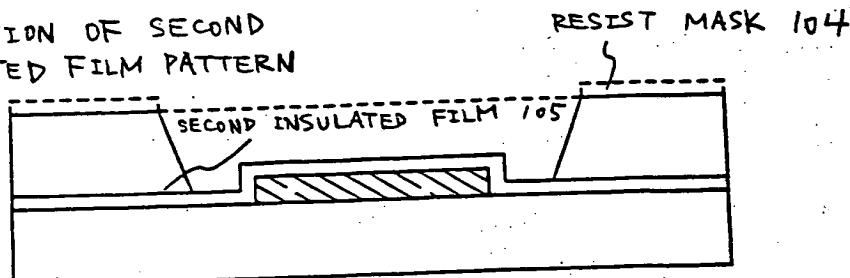


Fig. 2C FORMATION OF ORGANIC SEMICONDUCTOR FILM

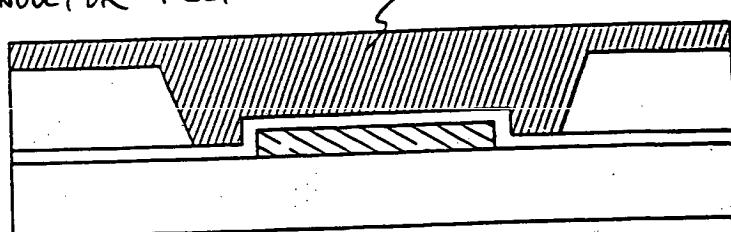


Fig. 2D FORMATION OF CHANNEL REGION

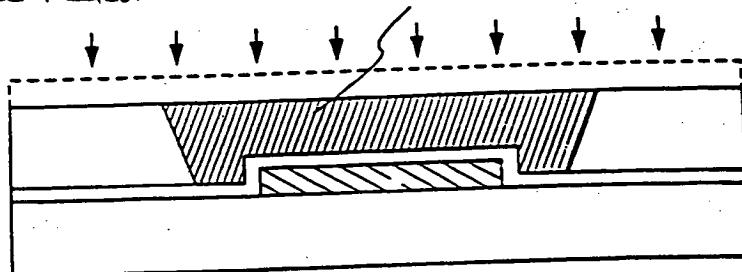
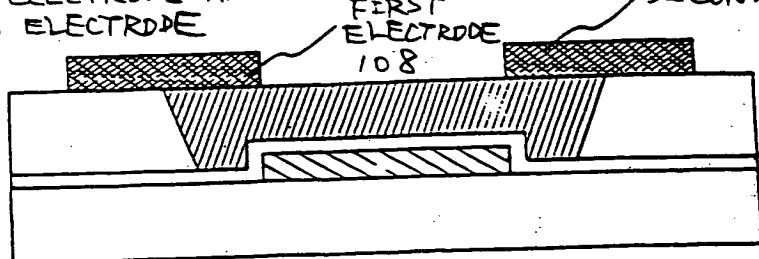
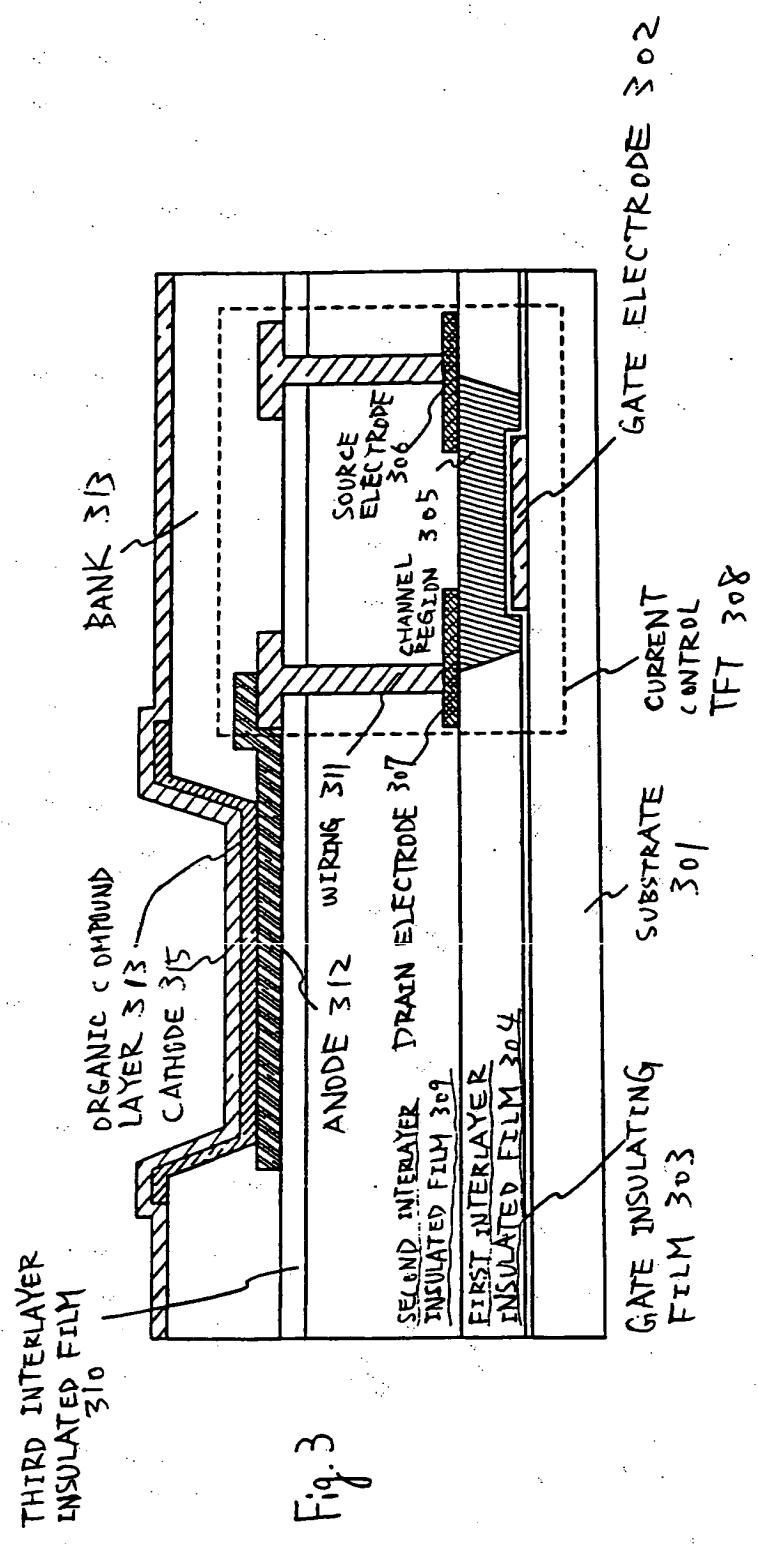


Fig. 2E FORMATION OF FIRST ELECTRODE AND SECOND ELECTRODE





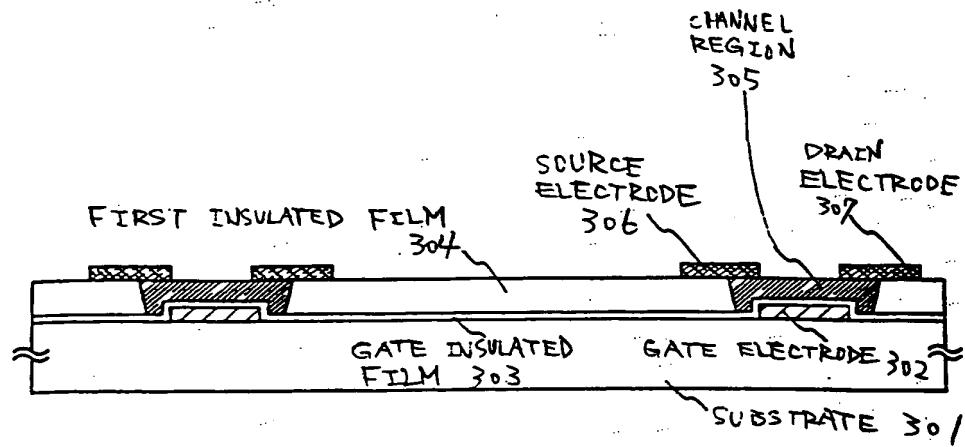


Fig. 4A

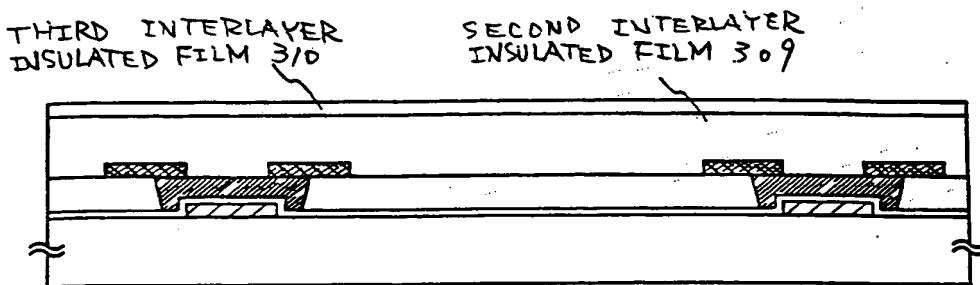


Fig. 4B

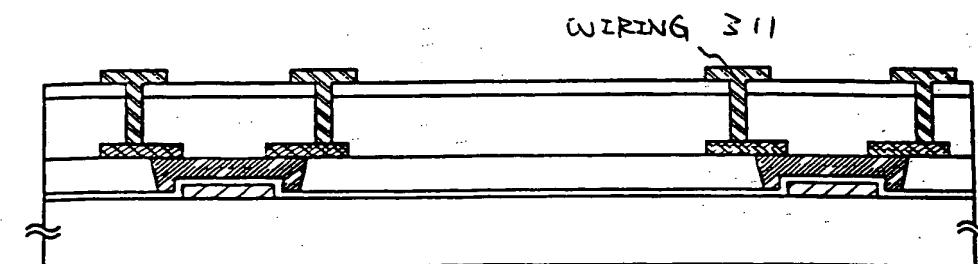


Fig. 4C

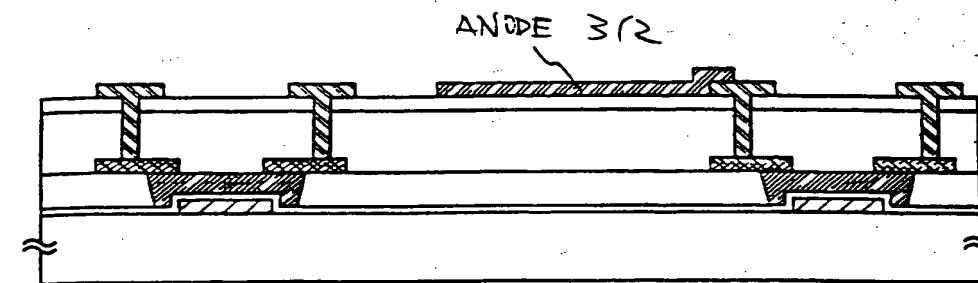


Fig. 4D

Fig. 5A

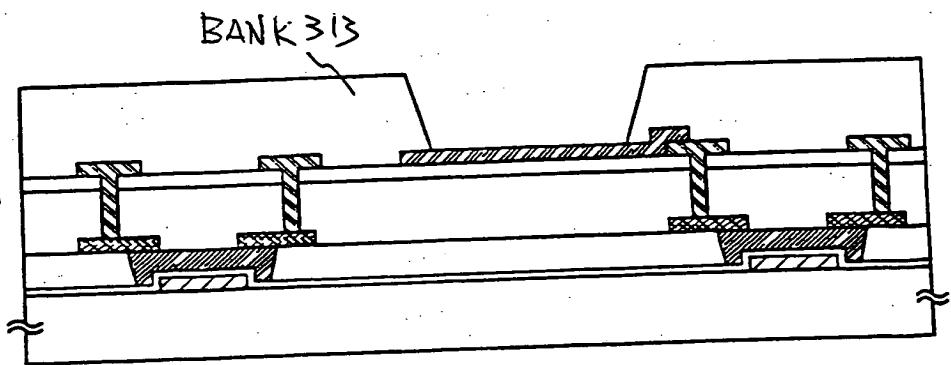


Fig. 5B

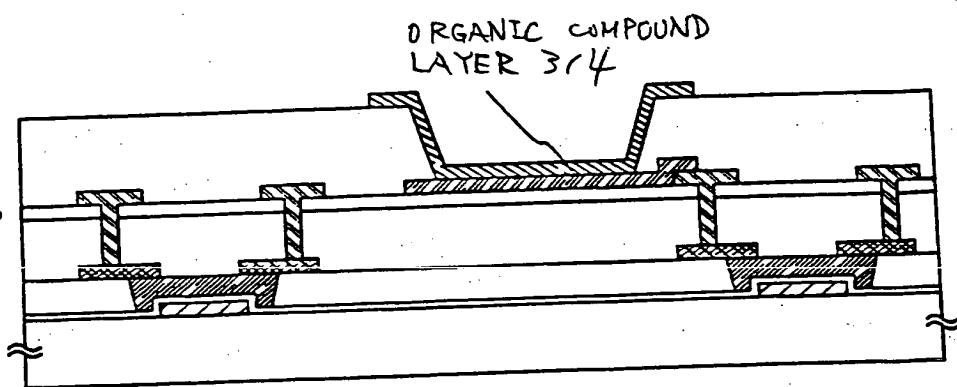
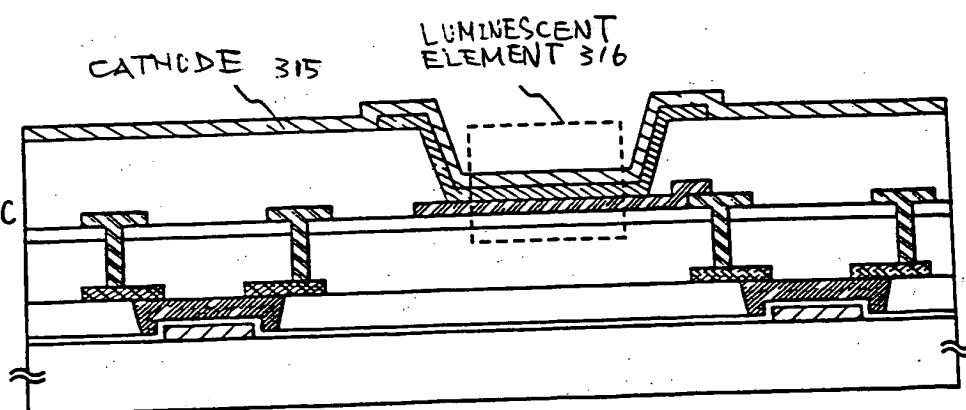


Fig. 5C



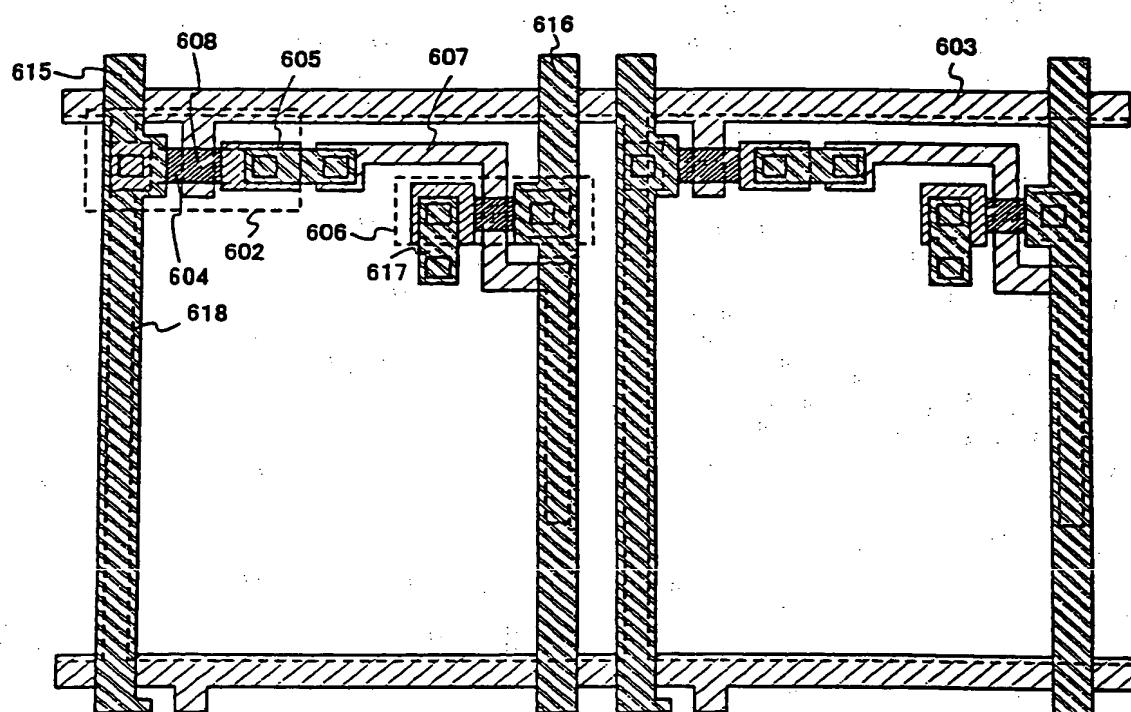


Fig. 6A

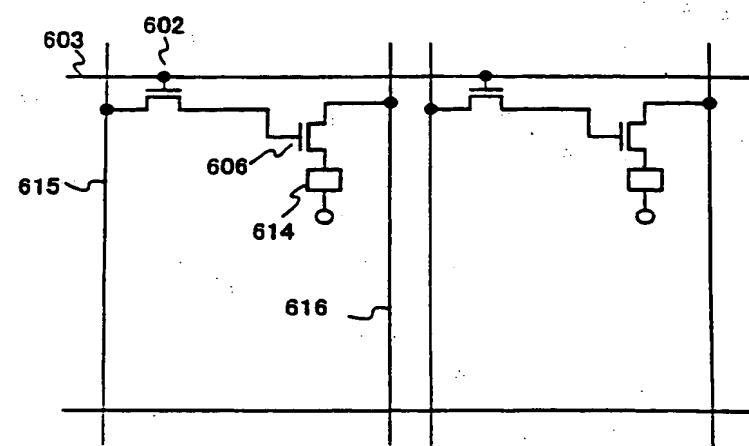
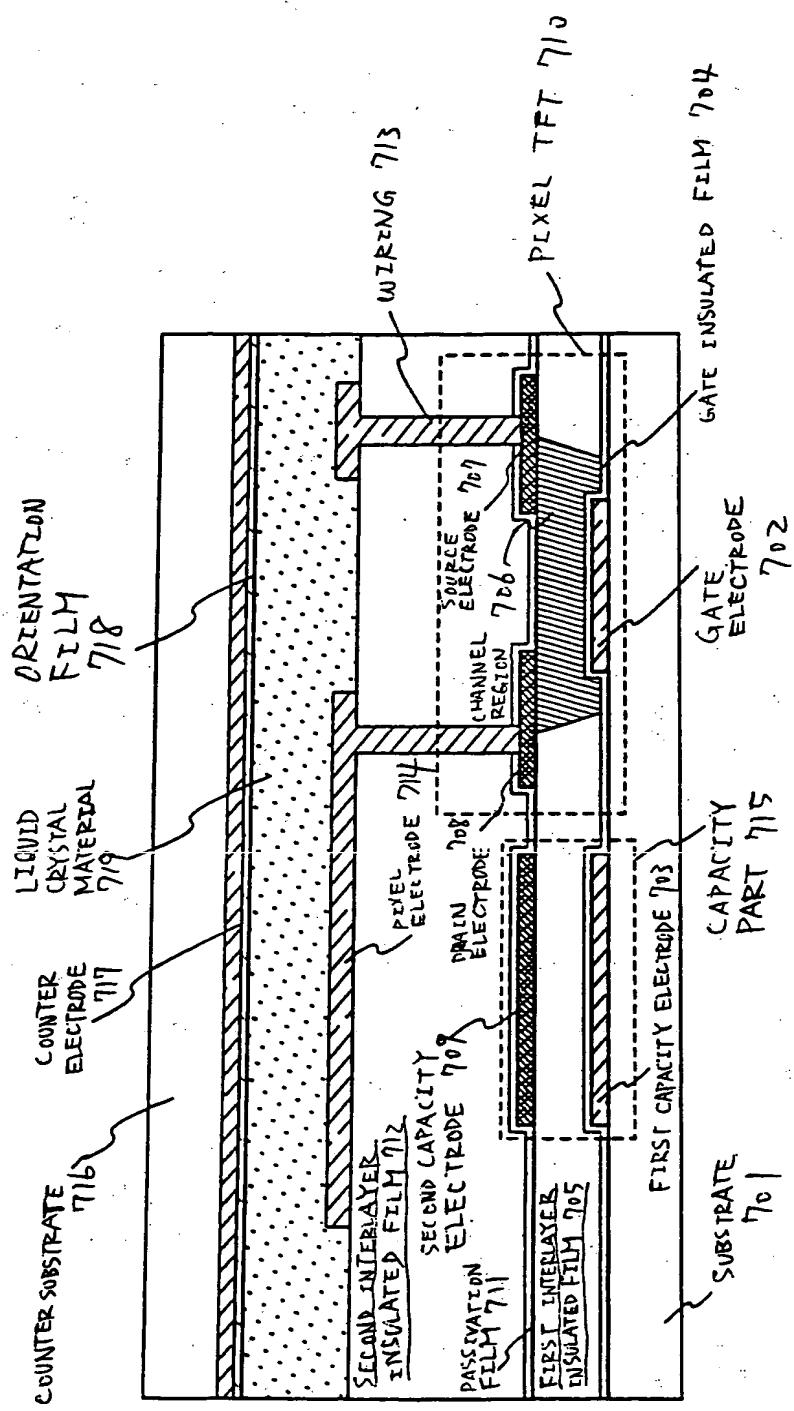
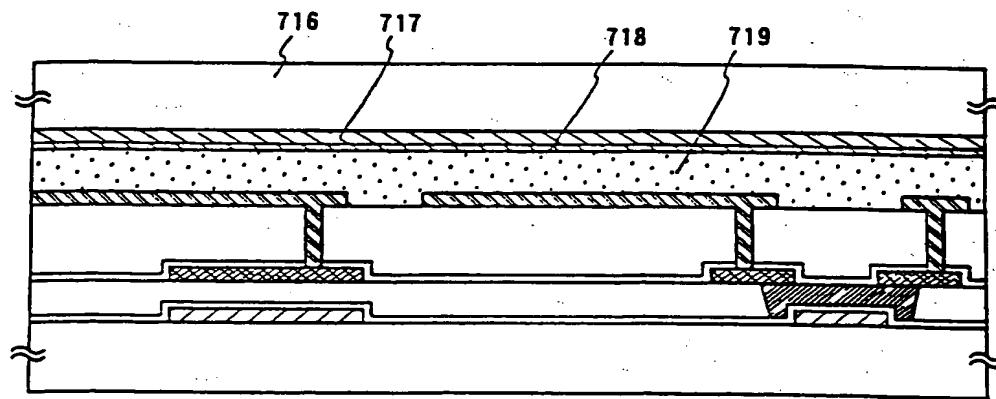
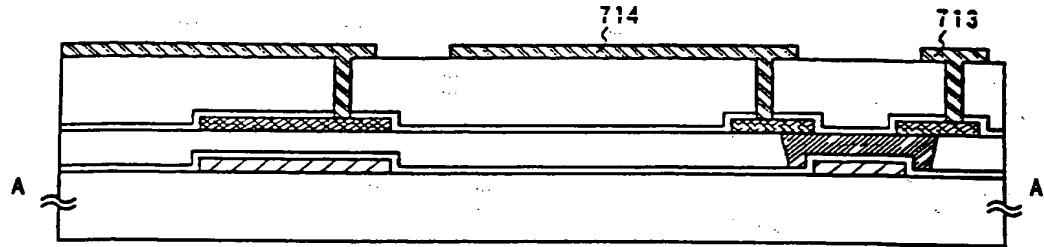
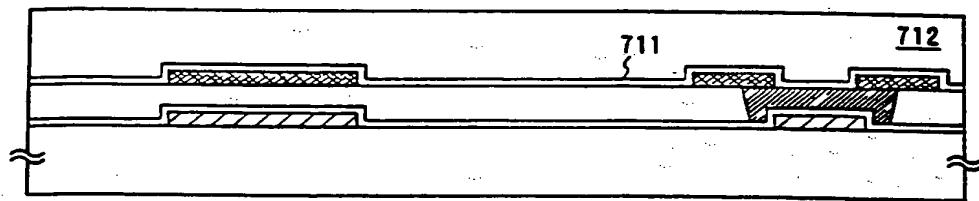
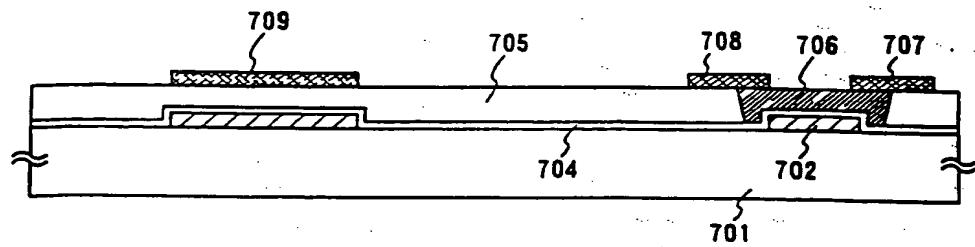


Fig. 6B





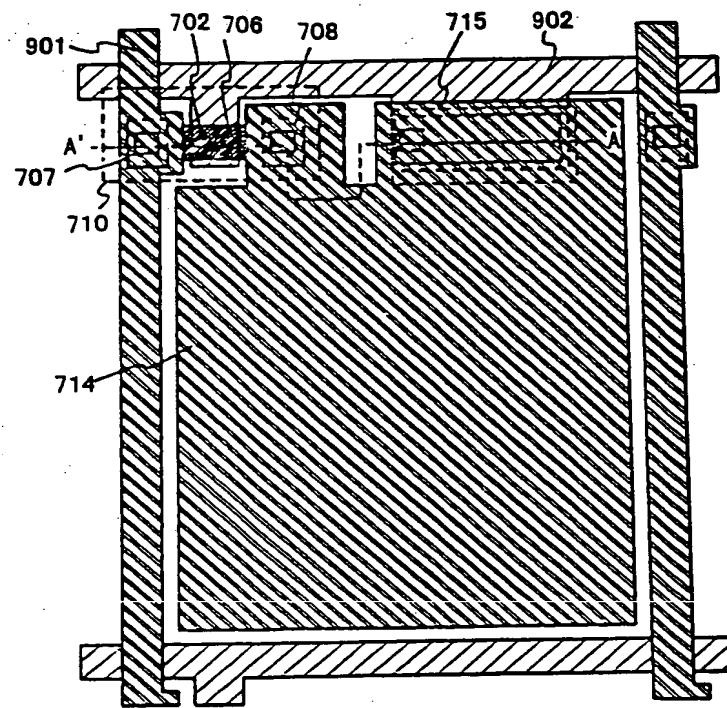


Fig. 9A

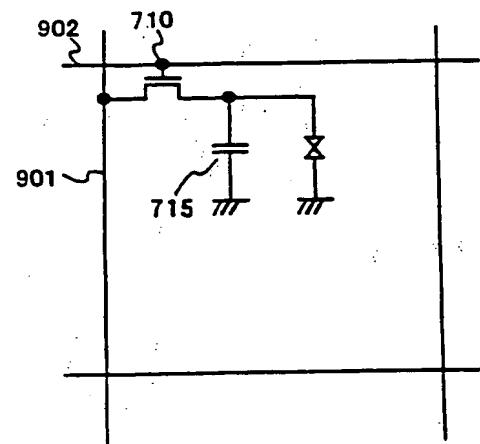


Fig. 9B

GATE SIGNAL LINE DRIVING CIRCUIT 1003

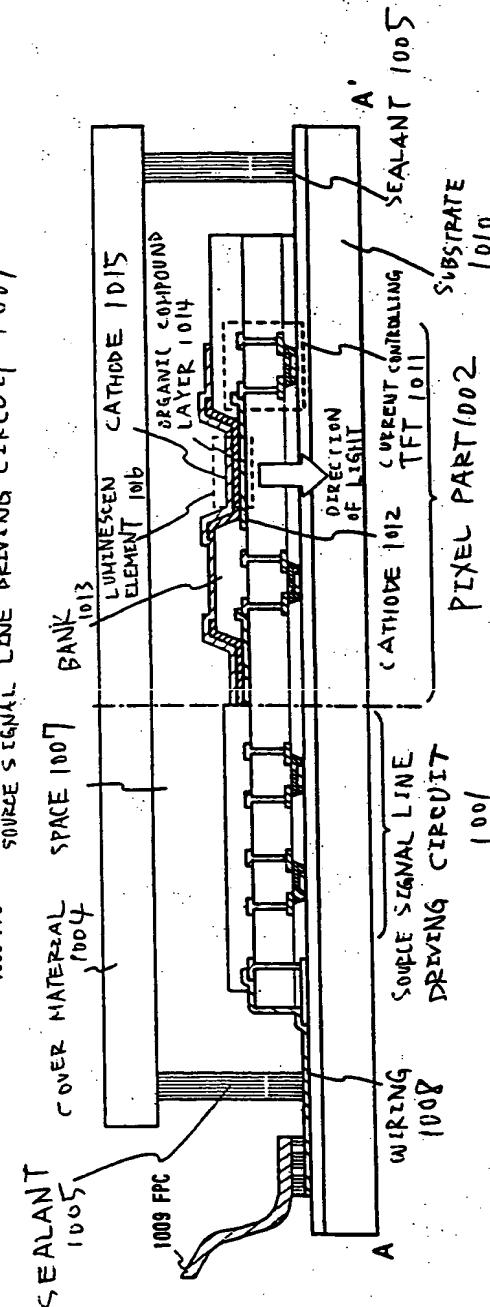
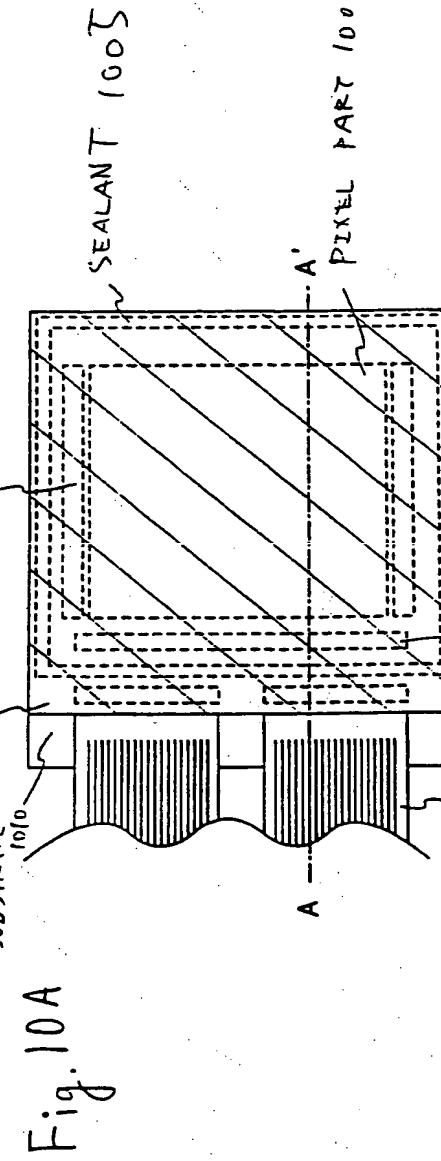


Fig. 11A

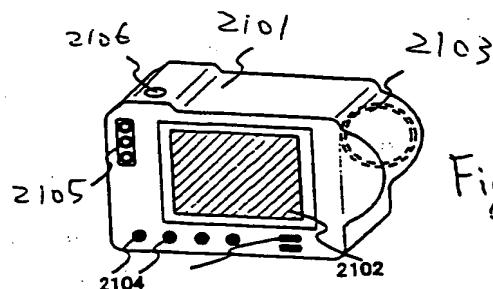
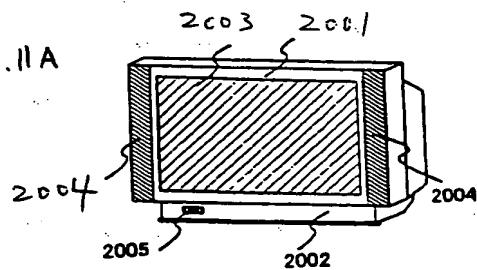


Fig. 11B

Fig. 11C

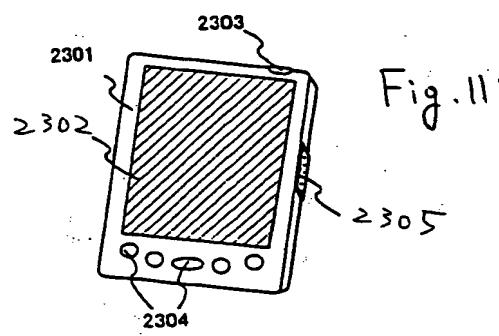
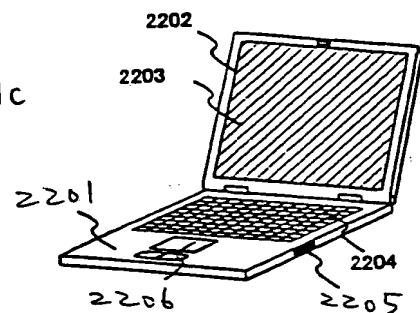


Fig. 11D

Fig. 11E

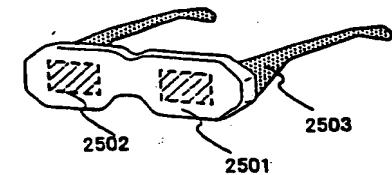
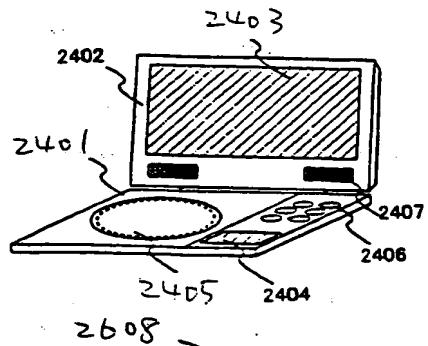
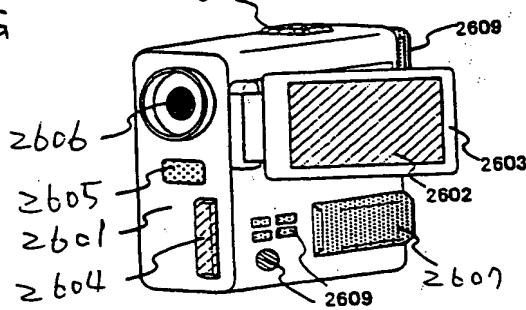


Fig. 11F

Fig. 11G



(H)

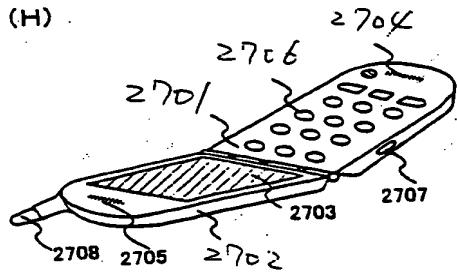


Fig. 11H